Unit in mm

## **TOSHIBA**

#### TOSHIBA PHOTOCOUPLER GaAlAs IRED & PHOTO-IC

# **TLP251F**

INVERTER FOR AIR CONDITIONOR

INDUCTION HEATING

TRANSISTOR INVERTER

POWER MOS FET GATE DRIVE

**IGBT GATE DRIVE** 

The Toshiba TLP251F consists of a GaAlAs light emitting diode and a integrated photodetector.

This unit is 8-lead DIP package.

TLP251F is suitable for gate driving circuit of IGBT or power MOS FET. Especially TLP251 is capable of "direct" gate drive of lower power IGBTs. (~15A)

• Input Threshold Current: IF=5mA (Max.)

• Supply Current : 11mA (Max.)

• Supply Voltage : 10~35V

Output Peak Current : ±0.4A (Max.)

• Switching Time :  $t_{pHL}$ ,  $t_{pLH} = 1 \mu s$  (Max.)

• Isolation Voltage : 2500V<sub>rms</sub> (Min.)

UL Recognized : UL1577, File No.E67349

• Option (D4) type

VDE Approved: DIN VDE0884/06.92, Certificate No.87447

Maximum Operating Insulation Voltage: 1140Vpk

Highest Permissible Over Voltage: 6000Vpk

(Note 1) When a VDE0884 approved type is needed, please designate the "Option (D4)"

Structural Parameter

Creepage Distance : 8.0mm (Min.) Clearance : 8.0mm (Min.)

11-10C402

Weight: 0.54g

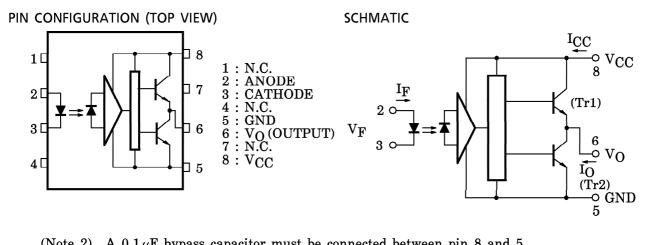
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### TRUTH TABLE

		Tr1	Tr2
Input LED	ON	ON	OFF
	OFF	OFF	ON



(Note 2) A  $0.1\mu\mathrm{F}$  bypass capacitor must be connected between pin 8 and 5.



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